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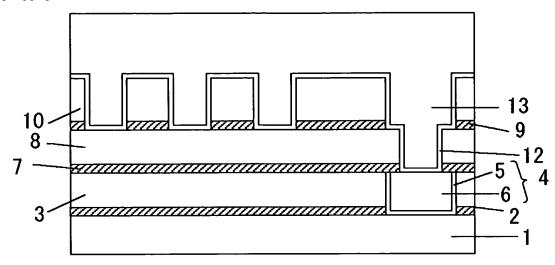
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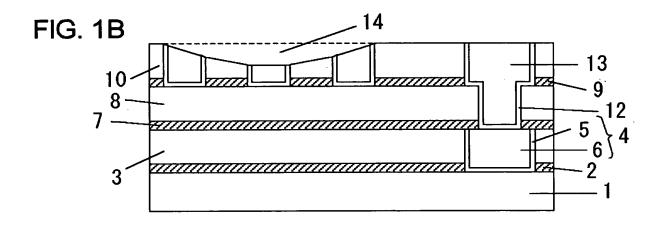
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FIG. 1A







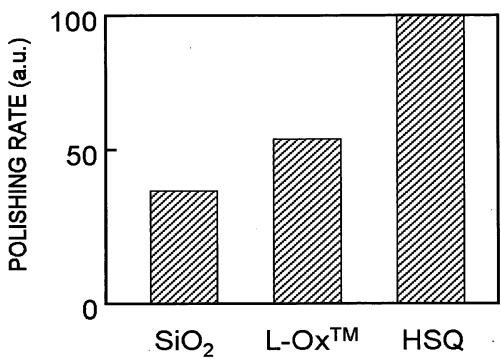


FIG. 3A

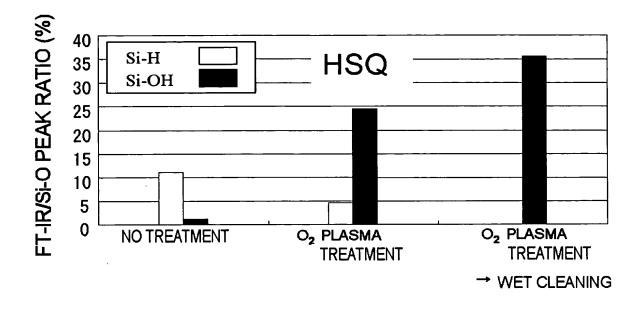


FIG. 3B

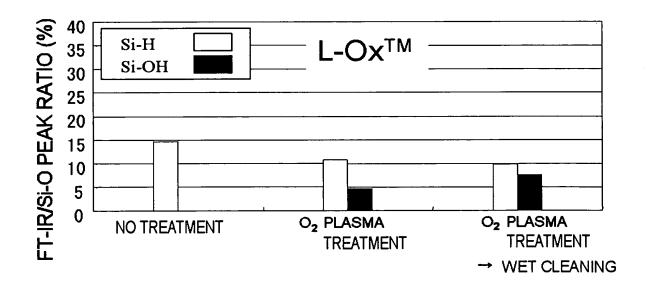
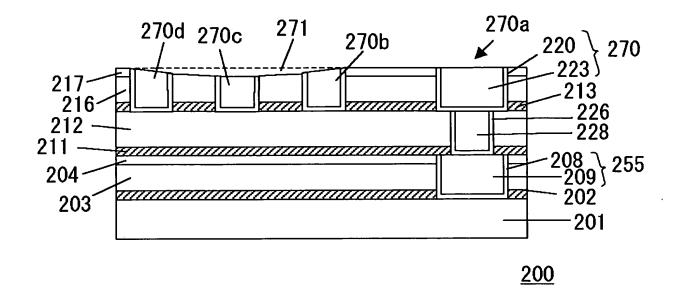
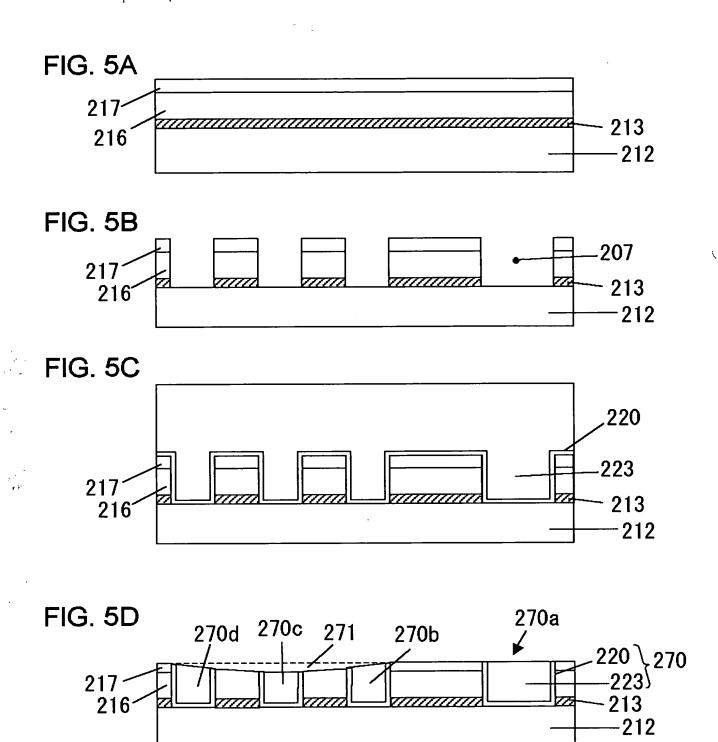


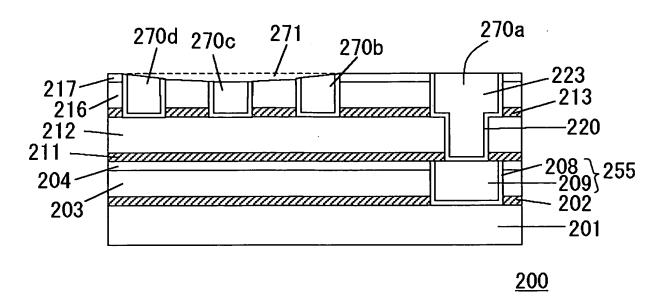
FIG. 4

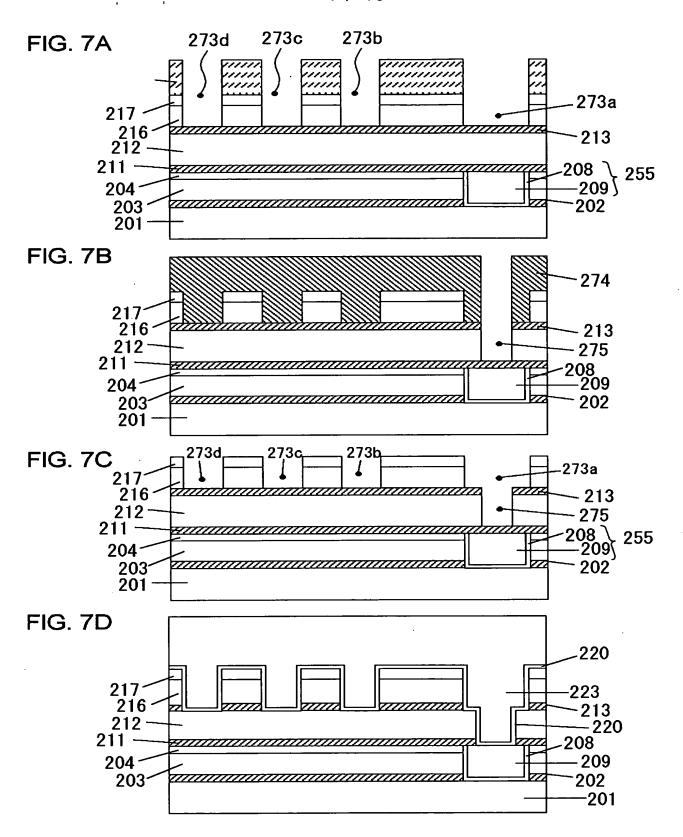




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FIG. 6







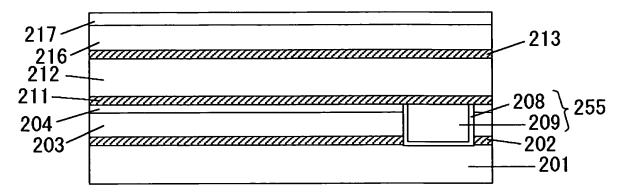


FIG. 8B

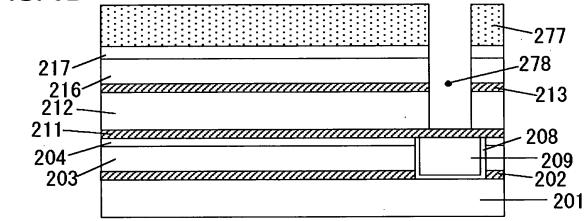
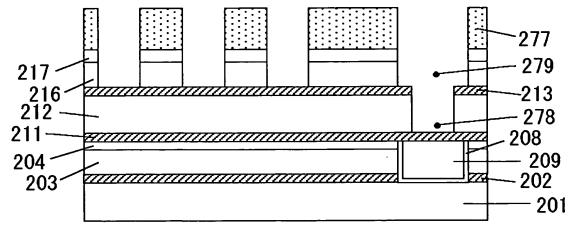
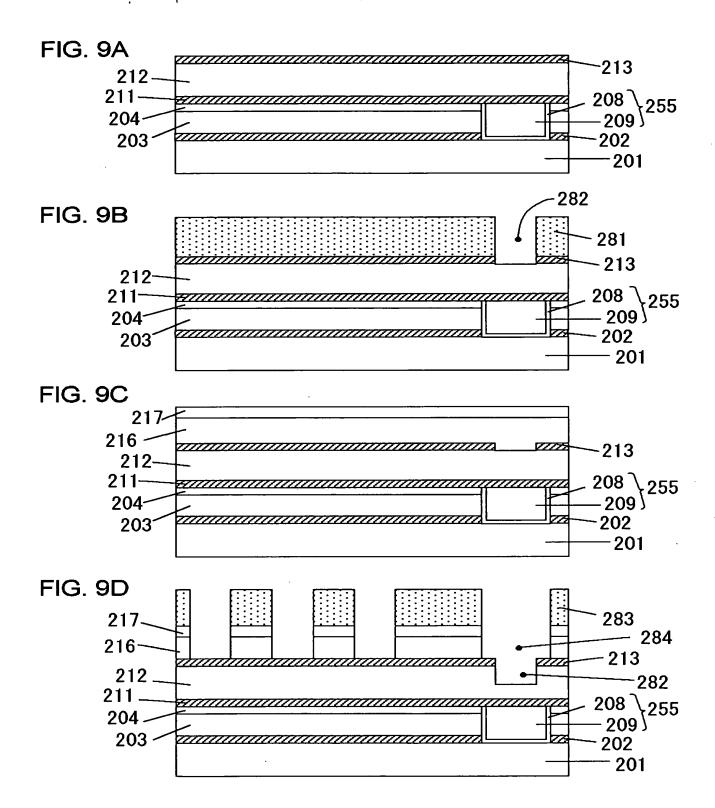


FIG. 8C







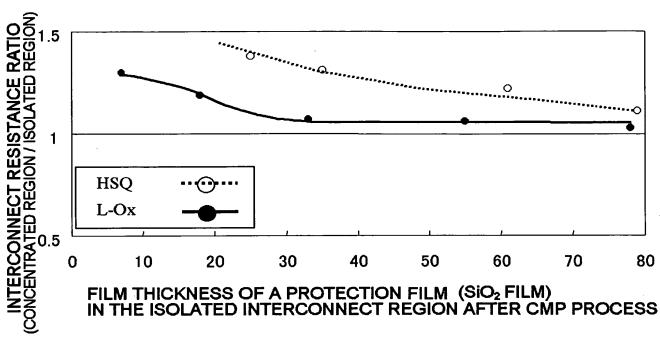
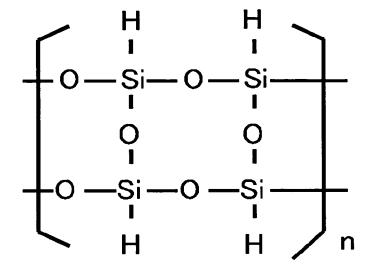


FIG. 11



Kazutoshi SHIBA et al. "Semiconductor Device and Method of Manufacturing the Same" Q79657-----Filed January 30, 2004

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FIG. 12

DIELECTRIC CONSTANT (@1MHz)	2. 9
REFRACTIVE INDEX (@633nm)	1. 39
STRESS (dyne/cm ²)	7. 00E+08
HARDNESS (GPa)	0. 9
ELASTIC MODULUS (GPa)	6
THERMAL EXPANSION COEFFICIENT (ppm/deg-C)	18
GLASS TRANSITION TEMPERATURE (deg-C)	none
THERMAL CONDUCTIVITY (W/m·K @25 deg-C)	0. 31

FIG. 13

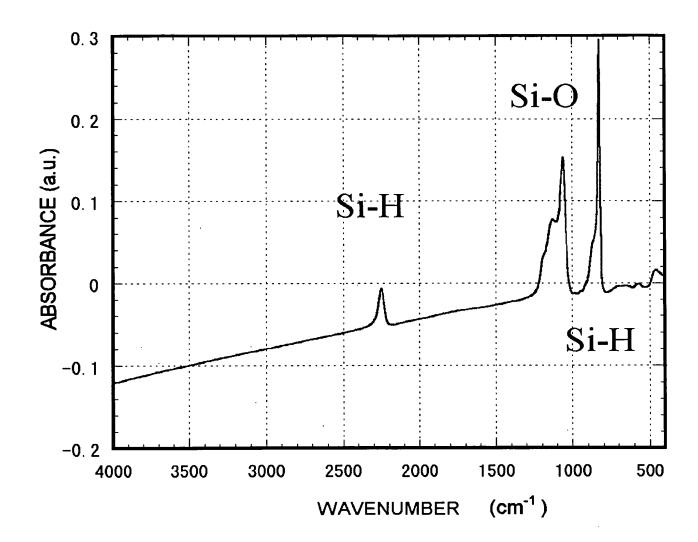


FIG. 14

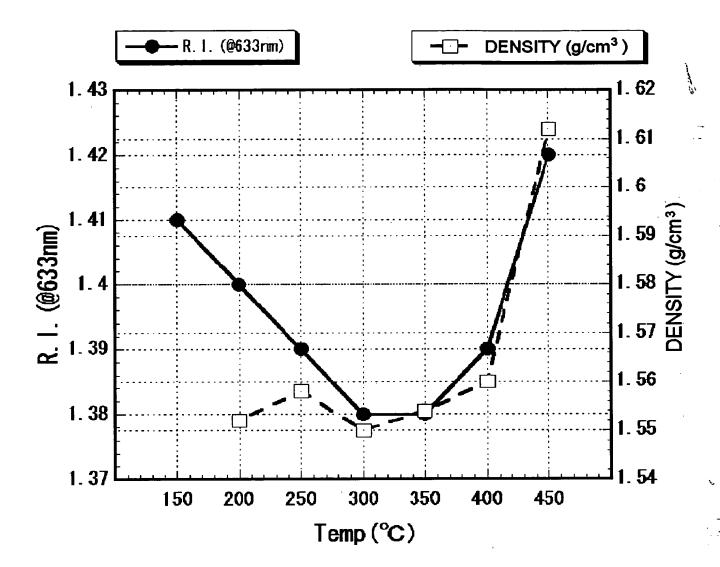


FIG. 15

